

Frequency Response

(Part 3)

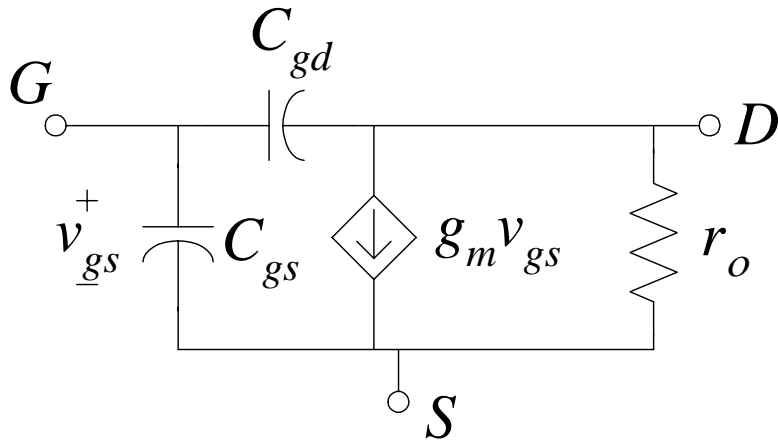
Dr. José Ernesto Rayas Sánchez

Most of the diagrams of this presentation were taken from the web site of the authors of the books:

A.R. Hambley, *Electronics: A Top-Down Approach to Computer-Aided Circuit Design*. Englewood Cliffs, NJ: Prentice Hall, 2000.

R.C. Jaeger, *Microelectronic Circuit Design*. New York, NY: McGraw-Hill, 1996.

The FET High-Frequency Model



$$g_m = 2K(V_{GS} - V_t)$$

$$r_o = \frac{|V_A|}{I_{DS}}$$

$$V_A = 1/\lambda$$

$$C_{iss} = C_{gs} + C_{gd} \quad (\text{input capacitance})$$

$$C_{oss} = C_{ds} + C_{gd} \quad (\text{output capacitance})$$

$$C_{rss} = C_{gd} \quad (\text{reverse capacitance})$$

The FET Unity-Gain Frequency (f_T)

It is the frequency at which the magnitude of the short-circuit current gain of the Common Source configuration becomes unity

$$f_T = \frac{g_m}{2\pi(C_{gs} + C_{gd})}$$

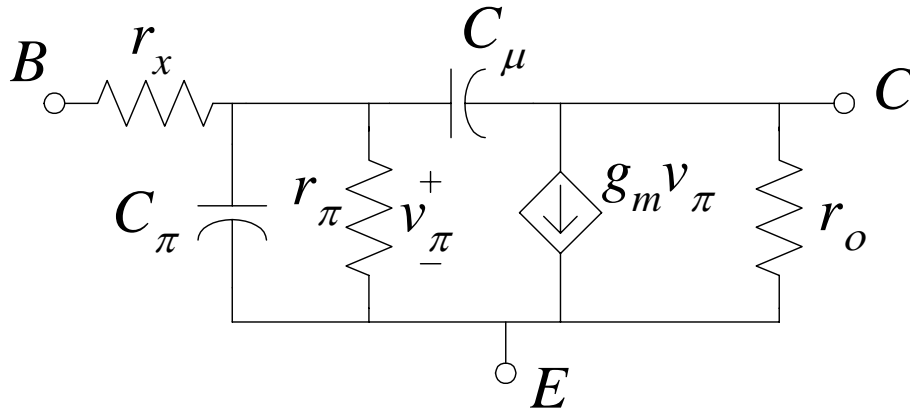
20 MHz $\leq f_T \leq$ 100 MHz for JFETs

100 MHz $\leq f_T \leq$ 2 GHz for MOSFETs

5 GHz $\leq f_T \leq$ 15 GHz for GaAs MESFETs

10 GHz $\leq f_T \leq$ 200 GHz for SiGe MOSFETs

The BJT High-Frequency Hybrid π Model



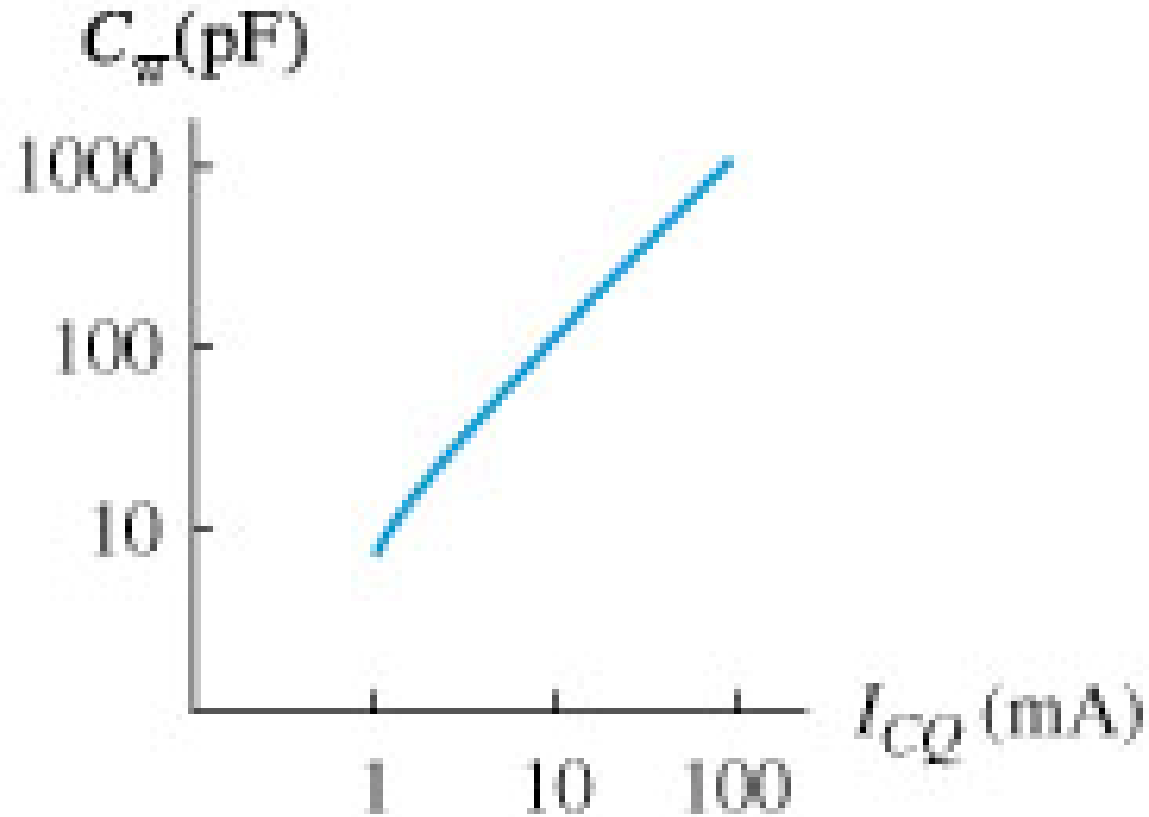
$$g_m = \frac{I_C}{V_T} \quad r_\pi = \frac{\beta}{g_m} \quad r_o = \frac{V_A}{I_C}$$

$$r_x = h_{ie} - r_\pi \quad r_\mu = r_\pi / h_{re}$$

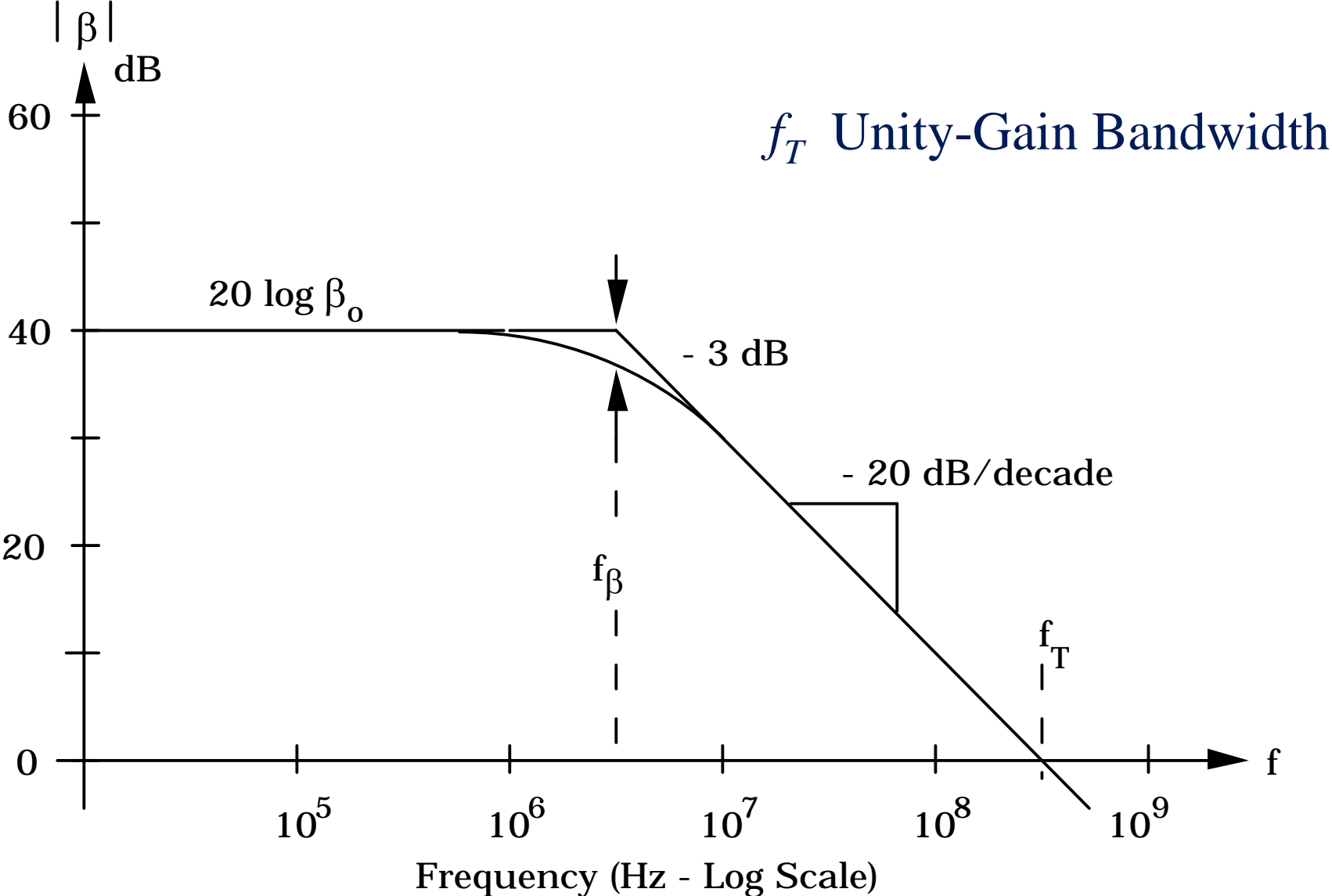
$$C_\mu = C_{ob} = C_{cb} \quad (\text{Collector-Base capacitance})$$

$$C_\pi = C_{eb} \quad (\text{Base-Emitter capacitance})$$

Typical Behaviour of C_{π}



Typical Behaviour of β



The BJT Unity-Gain Bandwidth (f_T)

It is the frequency at which the magnitude of the short-circuit current gain of the common emitter configuration becomes unity

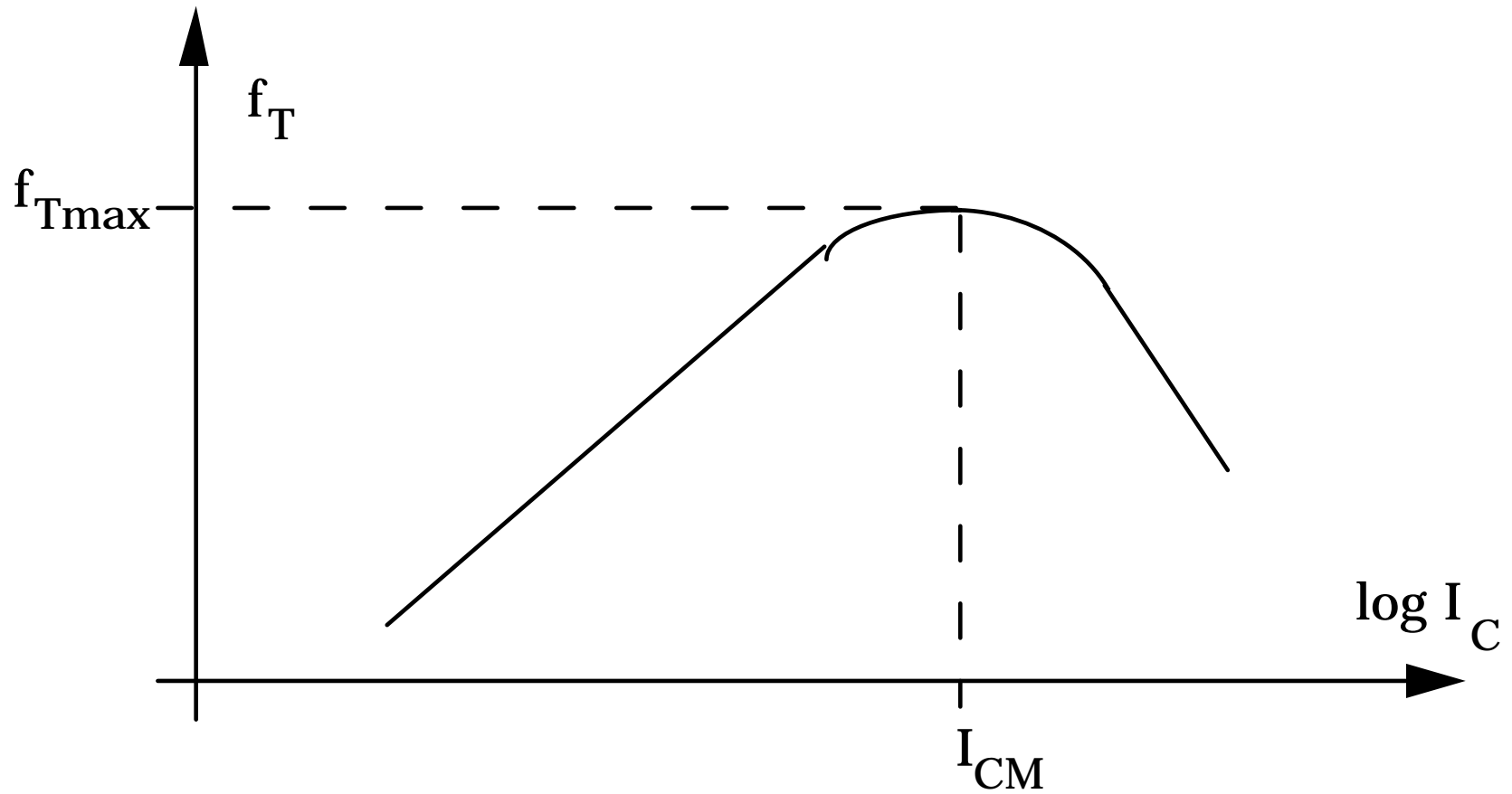
$$f_T = \frac{g_m}{2\pi(C_\pi + C_\mu)}$$

$2 \text{ MHz} \leq f_T \leq 100 \text{ MHz}$ for general purpose BJTs

$1 \text{ GHz} \leq f_T \leq 10 \text{ GHz}$ for high speed BJTs

$1 \text{ GHz} \leq f_T \leq 50 \text{ GHz}$ for HBTs and HEMTs

Typical Behaviour of f_T



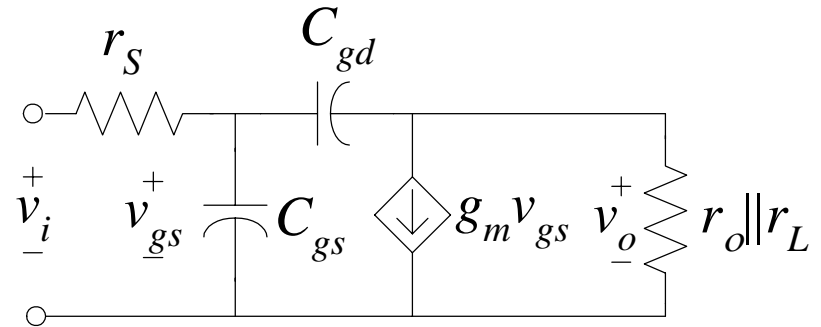
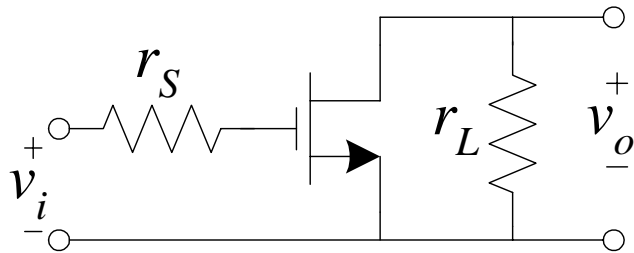
The Open-Circuit Time Constant Method (HF)

- 1) Replace the amplifier by its high frequency model
- 2) Calculate the resistance R_i in parallel with the capacitor C_i , considering all the remaining capacitors as open circuits
- 3) Repeat step 2) for each capacitor ($i = 1, 2, \dots, n_H$)
- 4) Calculate ω_H using

$$\omega_H \approx \frac{1}{\sum_{i=1}^{n_H} R_i C_i}$$

High-Frequency Response of FET Amplifiers

Common Source



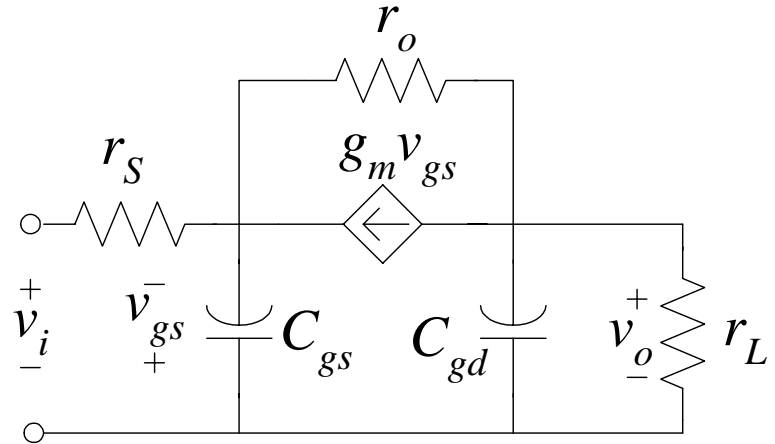
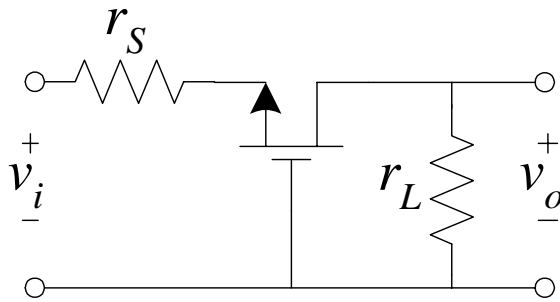
$$R_{gs} = r_S \qquad R_{gd} = \frac{v_{gs} - v_o}{v_{gs} / r_S} = r_S \left(1 - \frac{v_o}{v_{gs}}\right)$$

$$v_o = -\left(\frac{v_{gs}}{r_S} + g_m v_{gs}\right)(r_o \parallel r_L) \qquad R_{gd} = r_S [1 + (r_o \parallel r_L)(g_m + 1/r_S)]$$

$$\omega_H \approx 1 / (R_{gs} C_{gs} + R_{gd} C_{gd})$$

High-Frequency Response of FET Amplifiers

Common Gate



$$R_{gs} = r_S \parallel Z_1 \quad Z_1 = \frac{-v_{gs}}{v_o / r_L} \quad v_o = \left[-g_m v_{gs} + \left(\frac{-v_{gs} - v_o}{r_o} \right) \right] r_L$$

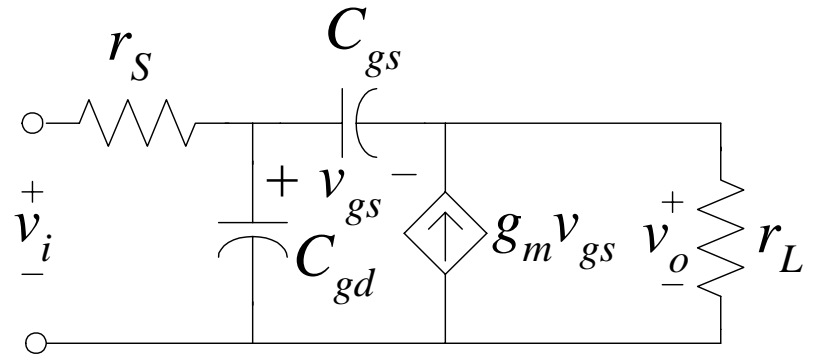
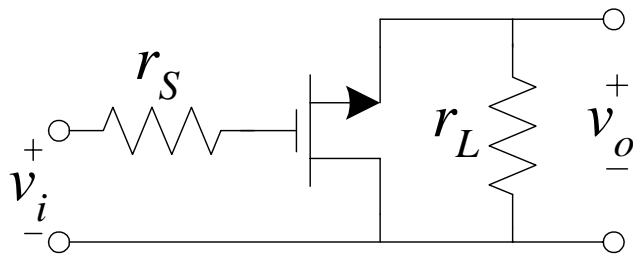
$$Z_1 = \frac{r_L (1 + r_L / r_o)}{g_m r_L + r_L / r_o} \quad \text{if } r_o \gg r_L \text{ then } Z_1 \approx \frac{1}{g_m}$$

To calculate R_{gd} , assume $r_o \gg r_S$, then $v_{gs} = 0$: $R_{gd} = r_o \parallel r_L$

$$\omega_H \approx 1 / (R_{gs} C_{gs} + R_{gd} C_{gd})$$

High-Frequency Response of FET Amplifiers

Common Drain



$$R_{gd} = r_S \quad R_{gs} = \frac{v_{gs}}{g_m v_{gs} - v_o / r_L}$$

$$\frac{v_{gs} + v_o}{r_S} = g_m v_{gs} - \frac{v_o}{r_L}$$

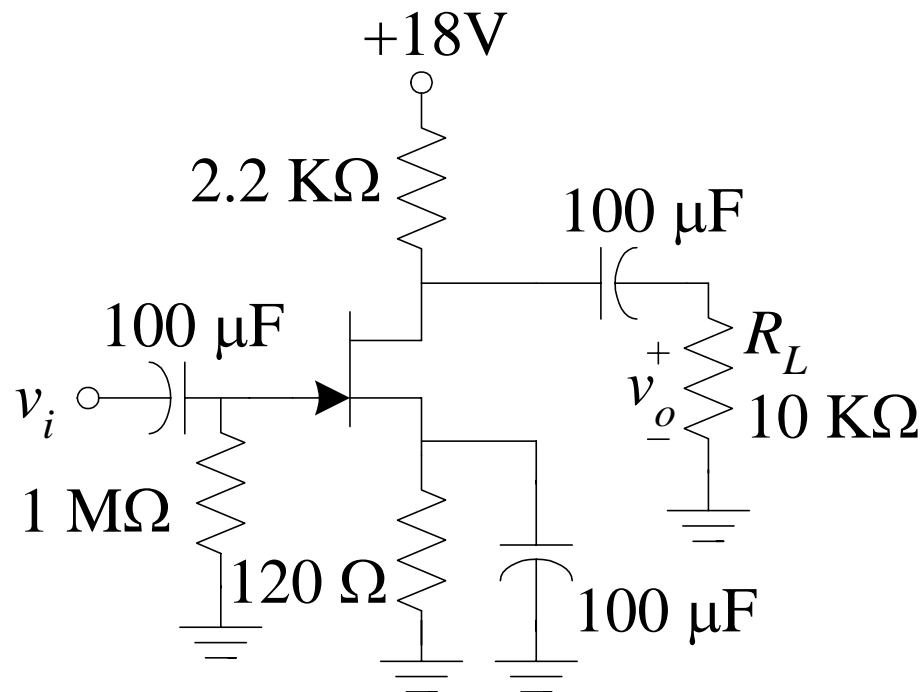
$$v_o = \frac{v_{gs} (g_m r_S - 1)}{1 + r_S / r_L} \approx \frac{-v_{gs}}{1 + r_S / r_L}$$

$$R_{gs} = \frac{1}{g_m + 1 / (r_L + r_S)} = \frac{r_L + r_S}{1 + g_m (r_L + r_S)}$$

$$\omega_H \approx 1 / (R_{gs} C_{gs} + R_{gd} C_{gd})$$

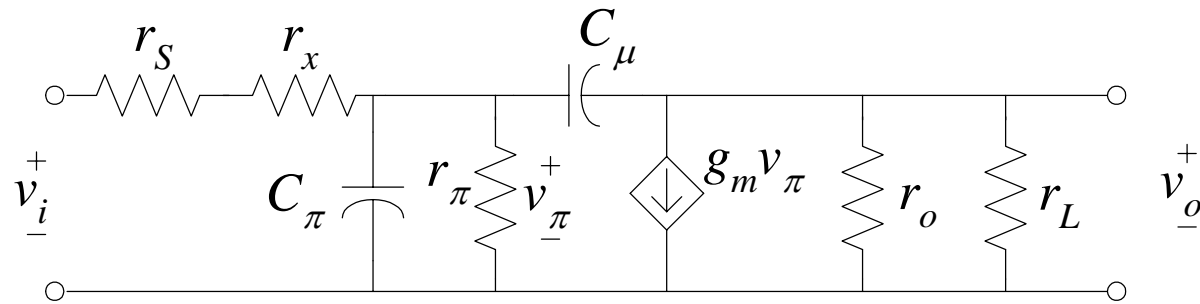
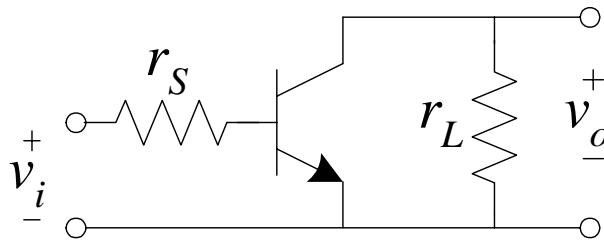
Example

Calculate the cutoff high-frequency for the following JFET amplifier (assume $V_P = -3$ V, $I_{DSS} = 7$ mA, $\lambda = 10^{-2}$ V⁻¹, $C_{gd} = 1$ pF, $C_{gs} = 3$ pF)



High-Frequency Response of BJT Amplifiers

Common Emitter



$$R_{\pi} = (r_S + r_x) \parallel r_{\pi}$$

$$R_{\mu} = \frac{v_{\pi} - v_o}{v_{\pi} / R_{\pi}} = R_{\pi} \left(1 - \frac{v_o}{v_{\pi}}\right)$$

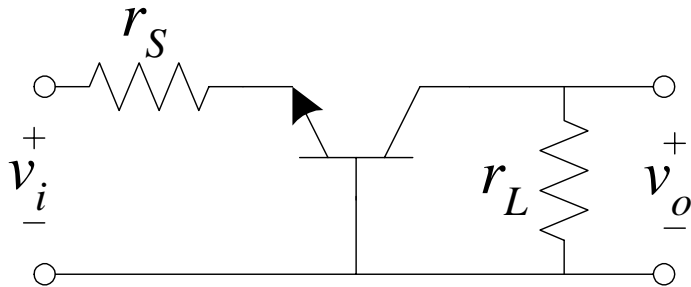
$$v_o = -\left(\frac{v_{\pi}}{R_{\pi}} + g_m v_{\pi}\right)(r_o \parallel r_L)$$

$$R_{\mu} = R_{\pi} [1 + (r_o \parallel r_L)(g_m + 1/R_{\pi})]$$

$$\omega_H \approx 1/(R_{\pi} C_{\pi} + R_{\mu} C_{\mu})$$

High-Frequency Response of BJT Amplifiers

Common Base



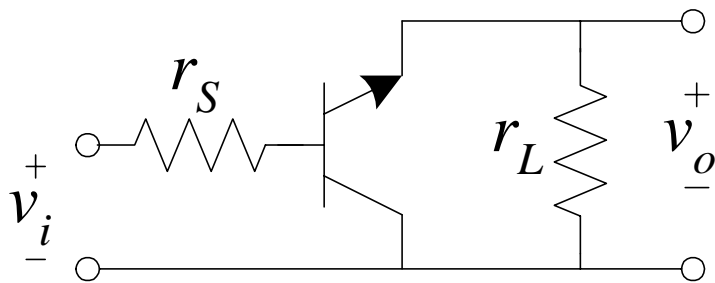
It can be shown that

$$R_{\pi} = r_{\pi} \parallel \frac{r_x + r_S}{1 + g_m r_S} \qquad R_{\mu} = r_L \parallel (r_o + r_x \parallel r_S) \approx r_L$$

$$\omega_H \approx 1/(R_{\pi} C_{\pi} + R_{\mu} C_{\mu})$$

High-Frequency Response of BJT Amplifiers

Common Collector



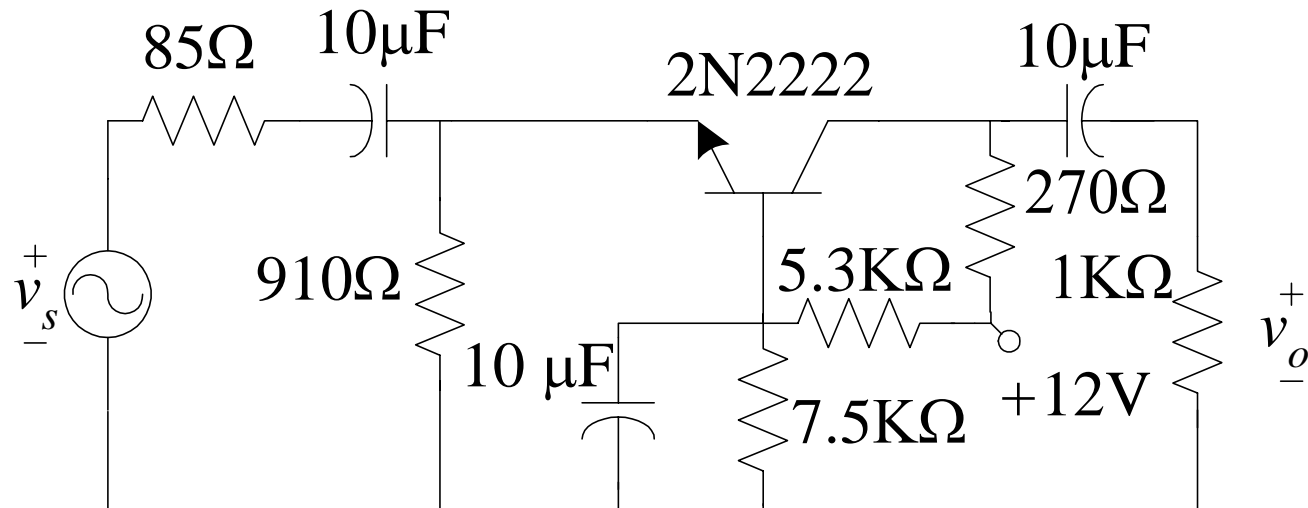
It can be shown that

$$R_{\pi} = r_{\pi} \parallel \frac{r_x + r_S + (r_L \parallel r_o)}{1 + g_m (r_L \parallel r_o)} \quad R_{\mu} = r_{\pi} \parallel \frac{r_L + r_S + r_x}{1 + g_m (r_L + r_S + r_x)}$$

$$\omega_H \approx 1 / (R_{\pi} C_{\pi} + R_{\mu} C_{\mu})$$

Example

Calculate the cutoff high-frequency for the following BJT amplifier



Assignment

Solve problems 7.41, 7.47, 7.54, 7.56, 7.67 and 7.68 from the textbook